

RoHS

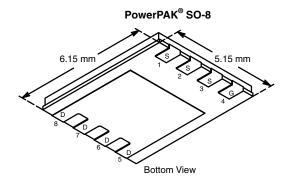
COMPLIANT HALOGEN

FREE

Vishay Siliconix

## N-Channel 150 V (D-S) MOSFET

PRODUC	T SUMMARY		
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
150	0.033 at V <sub>GS</sub> = 10 V	35	33 nC

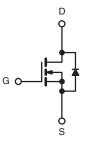


#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Primary Side Switch
- Isolated DC/DC Converters



N-Channel MOSFET

Ordering Information:

SiR838DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATIN</b>	<b>IGS</b> (T <sub>A</sub> = 25 °C	, unless othe	erwise noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	150	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
	T <sub>C</sub> = 25 °C		35		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	28		
Continuous Drain Current (1j = 150°C)	T <sub>A</sub> = 25 °C	טי	8.3 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	]	6.6 <sup>b, c</sup>	Α	
Pulsed Drain Current		I <sub>DM</sub>	60	A	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	L.	60 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	4.5 <sup>b, c</sup>		
Single Pulse Avalanche Current L = 0.1 mH		I <sub>AS</sub>	30		
Single Pulse Avalanche Energy		E <sub>AS</sub>	45	mJ	
	T <sub>C</sub> = 25 °C		96		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	62	w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C		5.4 <sup>b, c</sup>	vv	
	T <sub>A</sub> = 70 °C		3.5 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	<u></u>	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260		

THERMAL RESISTANCE RATI	NGS				
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	18	23	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1	1.3	0/11

Notes:

a. Package limited

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 65 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$	150			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA		175		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η - 200 μλ		-9		mv/ C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2		4	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zara Cata Valtaga Drain Current	1	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1	μA	
Zero Gate Voltage Drain Current	DSS	$V_{DS}$ = 150 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	30			А	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.3 A		0.0275	0.0330	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 8.3 A		28		S	
Dynamic <sup>b</sup>			•				
Input Capacitance	C <sub>iss</sub>			2075			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 75 V, $V_{GS}$ = 0 V, f = 1 MHz		155		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			45		pF nC	
Total Gate Charge	Qg			33	50		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 75 V, $V_{GS}$ = 10 V, $I_{D}$ = 8.3 A		14		nC	
Gate-Drain Charge	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	4					
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.3	1.4	2.8	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 75 V, $R_L$ = 11.5 $\Omega$		11	17		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ 6.6 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 1 $\Omega$		23	35	ns	
Fall Time	t <sub>f</sub>			10	15	1	
Drain-Source Body Diode Characteristic	s		•				
Continuous Source-Drain Diode Current	۱ <sub>S</sub>	T <sub>C</sub> = 25 °C			60	A	
Pulse Diode Forward Current	I <sub>SM</sub>				60		
Body Diode Voltage	V <sub>SD</sub>	$I_{\rm S} = 6.6$ A, $V_{\rm GS} = 0$ V		0.8	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	$\begin{array}{c c} I_{SM} & & & 60 \\ \hline V_{SD} & I_S = 6.6 \text{ A}, V_{GS} = 0 \text{ V} & & 0.8 \\ \hline \end{array} $		116	ns		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	- I <sub>F</sub> = 6.6 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C		260	390	nC	
Reverse Recovery Fall Time	ta	$F = 0.0 \text{ A}, \text{ u/ul} = 100 \text{ A/}\mu\text{s}, T_{\text{J}} = 25 \text{ °C}$		60			
Reverse Recovery Rise Time	t <sub>b</sub>			17		ns	

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing.

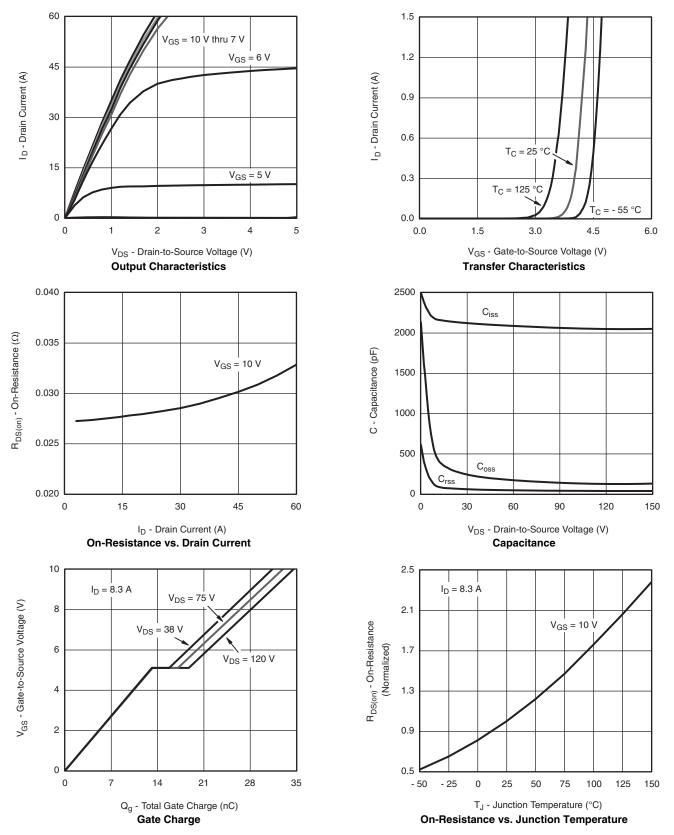
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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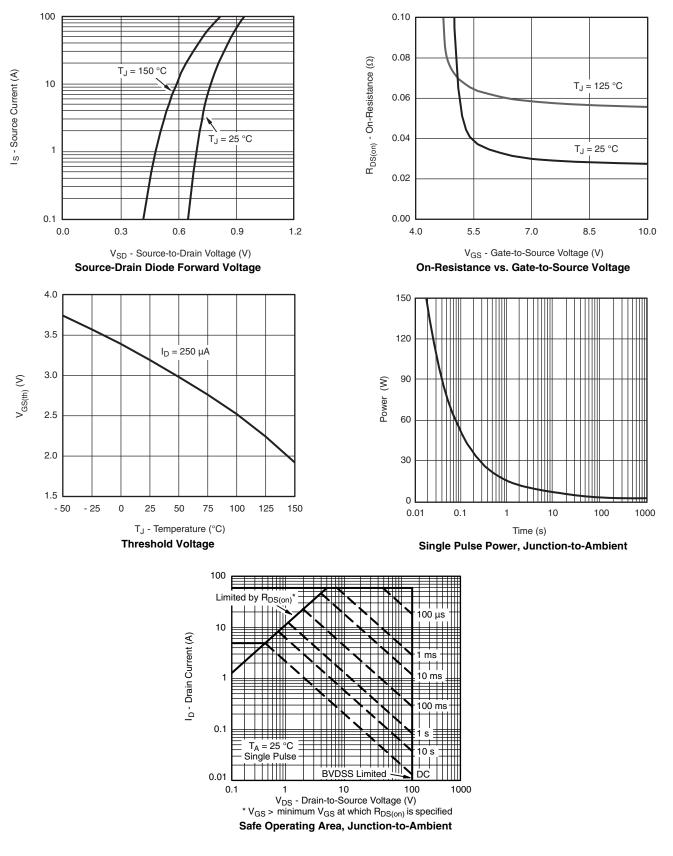
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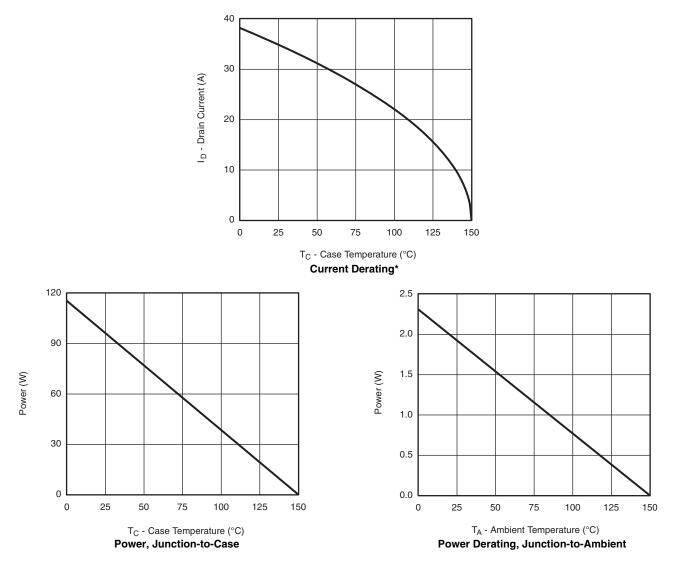
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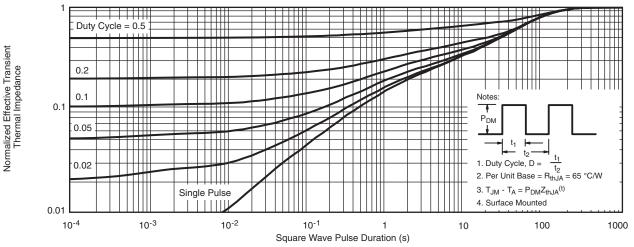


\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

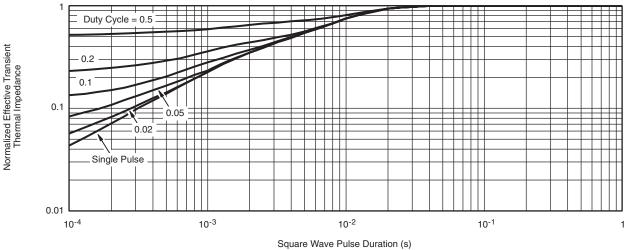


#### **Vishay Siliconix**

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65650">www.vishay.com/ppg?65650</a>.

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## PowerPAK<sup>®</sup> SO-8, (Single/Dual)









Backside View of Dual Pad

Notes

1. Inch will govern.

2 Dimensions exclusive of mold gate burrs.

3. Dimensions exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4	0.57 typ.				0.0225 typ.		
D5		3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)		0.58 typ.		0.023 typ.			
E4 (for other product)	0.75 typ.			0.030 typ.			
е	1.27 BSC			0.050 BSC			
K (for AL product)	1.45 typ.			0.057 typ.			
K (for other product)	1.27 typ.			0.050 typ.			
K1	0.56	-	-	0.022	-	-	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			

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# Application Note 826

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#### RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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